PNP/NPN Epitaxial Planar Silicon Transistors



2SA1580/2SC4104

# **High-Definition CRT Display Applications**

### **Features**

- · High f<sub>T</sub>.
- · Small reverse transfer capacitance.
- · Adoption of FBET process.

## **Package Dimensions**

unit:mm



():2SA1580

## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)70	V
Collector-to-Emitter Voltage	VCEO		(–)60	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)4	V
Collector Current	ΙC		(–)50	mA
Collector Current (Pulse)	I <sub>CP</sub>		(–)100	mA
Collector Dissipation	PC		200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)40V, I <sub>E</sub> =0			(–)0.1	μA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)3V, I <sub>C</sub> =0			(–)1.0	μA
DC Current Gain	hFE	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)10mA	60*		270*	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)10mA	350	700		MHz
Base-to-Collector Time Constant	r <sub>bb</sub> ',c <sub>c</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)10mA		8		ps
Output Capacitance	Cob	V <sub>CB</sub> =(-)10V, f=1MHz		1.3		pF
				(1.7)		pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		1.0		pF
				(1.3)		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =(-)20mA, I <sub>B</sub> =(-)2mA			0.5	V
					(-0.6)	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)20mA, I <sub>B</sub> =(-)2mA			(–)1.0	V
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0	(–)70			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(–)1mA, R <sub>BE</sub> =∞	(–)60			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0	(–)4			V

\* : The 2SA1580/2SC4104 are classified by 10mA h<sub>FE</sub> as follows :

90 4 180 135 5 270

60 3 120

Marking 2SA1580 : QL 2SC4104 : YY

 $h_{FE}$  rank : 3,4,5

SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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